

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A manufacturing method for a liquid crystal display ~~panel panels~~ having a high aperture ratio, comprising ~~the steps of:~~

providing a transparent substrate with thin film transistors formed ~~forming~~ therein, ~~and the~~ a periphery of the transparent substrate having an outer lead bonding area formed by covering an insulation layer over metal wires;

forming a protection layer over the thin film transistors of the transparent substrate and the outer lead bonding area;

applying a photo-etching process ~~[[by]]~~ using a half-tone mask to the protection layer so as to form openings respectively above the thin film transistors and at the outer lead bonding area, wherein ~~remove a part of the protection layer at the outer lead bonding area for exposing the insulation layer on which~~ at the outer lead bonding pads ~~are predefinedly located~~ area is exposed through the openings; and

expanding the openings by further etching the ~~remaining~~ protection layer and the exposed insulation layer ~~for exposing upper portions of the insulation layer and generating so as to form~~ via holes ~~through the insulation layer so as to expose~~ exposing

portions of the thin film transistors and the metal wires.

Claim 2 (Canceled)

Claim 3 (Currently Amended): The manufacturing method for a liquid crystal display panel ~~panels~~ having a high aperture ratio of Claim 1 ~~[[2]]~~, further comprising ~~the step~~ ~~eff[[:]]~~ forming a transparent conductive layer on the protection layer and inside the via holes so as to electrically contact the thin film transistors.

Claim 4 (Currently Amended): The manufacturing method for a liquid crystal display panel ~~panels~~ having a high aperture of Claim 1, wherein the thin film transistors are transistors ~~transistor is a transistor~~ having an etching stop structure.

Claim 5 (Currently Amended): The manufacturing method for a liquid crystal display panel ~~panels~~ having a high aperture ratio of Claim 1, wherein the thin film transistors are transistors ~~transistor is a transistor~~ having a back-channel etching structure.

Claim 6 (Currently Amended): The manufacturing method for a liquid crystal display panel ~~panels~~ having a high aperture of Claim 1, wherein the exposed portions of the metal wires are ~~[[the]]~~ outer lead bonding pads.

Claim 7 (Currently Amended): The manufacturing method for a liquid crystal display panel ~~panels~~ having a high aperture of Claim 1, wherein the protection layer is made from a transparent organic material.

Claim 8 (Currently Amended): The manufacturing method for a liquid crystal display ~~panel~~ ~~panels~~ having a high aperture of Claim 7, wherein the transparent organic material is acrylate.

Claim 9 (Currently Amended): The manufacturing method for a liquid crystal display ~~panel~~ ~~panels~~ having a high aperture ratio of Claim 1, further comprising ~~the step of~~[[:]] sealing the liquid crystal display panel by pasting a sealant on the ~~exposed portions of~~ the insulation layer at the outer lead bonding area.

Claim 10 (Currently Amended): The manufacturing method for a liquid crystal display ~~panel~~ ~~panels~~ having a high aperture ratio of Claim 1, further comprising ~~the step of~~[[:]] interposing a silicon nitride layer between the insulation layer and the protection layer.

Claim 11 (Currently Amended): The manufacturing method for a liquid crystal display ~~panel~~ ~~panels~~ having a high aperture ratio of Claim 1, wherein the protection layer is a photoresist layer.